What is claimed is:

1. A method for fabricating a thin film magnetic head, comprising the steps of:

fabricating a thin film magnetic head assembly on a given substrate,

fabricating, on said substrate, an electrical circuit including a circuit leading wire so as to monitor the processing degree of said thin film magnetic head assembly,

forming a protective layer so as to cover said thin film magnetic head assembly and said electrical circuit,

fabricating, on said substrate, a bump so as to penetrate said protective layer and thus, to be exposed,

fabricating, on said substrate, an element leading wire a circuit leading wire to be electrically connected to said thin film magnetic head assembly, and

electrically connecting said element leading wire and said circuit leading wire,

whereby said bump is shared with said thin film magnetic head assembly and said electrical circuit, and the processing degree of said thin film magnetic head assembly is indirectly monitored by an external monitoring system on the monitoring information from said electrical circuit to said external monitoring system via said bump.

2. A fabricating method as defined in claim 1, further comprising the step of forming a conductive film to electrically connect said element leading wire and said circuit leading wire.

3. A fabricating method as defined in claim 2, wherein said conductive film is made by a sputtering method or a plating method.

4. A fabricating method as defined in claim 2, wherein said element leading wire, said circuit leading wire and said conductive film are made of the same conductive material.

5. A fabricating method as defined in claim 1, further comprising the step of fabricating a bonding pad on said protective layer so as to be electrically connected with said bump.

6. A fabricating method as defined in claim 5, wherein said bonding pad is elongated, on said protective layer, to the area of said electrical circuit.

7. A fabricating method as defined in claim 6, wherein said bonding pad is narrowed in the area between said thin film magnetic head assembly and said electrical circuit.

8. A fabricating method as defined in claim 1, wherein said electrical circuit is constructed of an electrical lap-guiding element.

9. A fabricating method as defined in claim 8, wherein said thin film magnetic head assembly includes a reading head element, and the polishing degree of said reading head element is monitored by said electrical lap-guiding element.

10. A wafer structure comprising:

a thin film magnetic head assembly which is fabricated on a given substrate,

an electrical circuit including a circuit leading wire so as to monitor the processing degree of said thin film magnetic head assembly, which is fabricated on said substrate,

a protective layer so as to cover said thin film magnetic head assembly and said electrical circuit,

a bump so as to penetrate said protective layer and thus, to be exposed, which is fabricated on said substrate, and

an element leading wire to be electrically connected to said thin film magnetic head element to be connected to an external circuit, which is fabricated on said substrate

said element leading wire being electrically connected with said circuit leading wire,

said bump is shared with said thin film magnetic head assembly and said electrical circuit.

11. A wafer structure as defined in claim 10, further comprising a conductive film to electrically connect said element leading wire and said circuit leading wire.

12. A wafer structure as defined in claim 11, wherein said conductive film is made by a sputtering method or a plating method.

13. A wafer structure as defined in claim 12, wherein said element leading wire, said circuit leading wire and said conductive film are made of the same conductive material.

14. A wafer structure as defined in claim 10, further comprising a bonding pad on said protective layer so as to be electrically connected with said bump.

15. A wafer structure as defined in claim 14, wherein said bonding pad is elongated, on said protective layer, to the area of said electrical circuit.

16. A wafer structure as defined in claim 15, wherein said bonding pad is narrowed in the area between said thin film magnetic head assembly and said electrical circuit.

17. A wafer structure as defined in claim 10, wherein said electrical circuit is constructed of an electrical lap-guiding element.

18. A wafer structure as defined in claim 17, wherein said thin film magnetic head assembly includes a reading head element, and the polishing degree of said reading head element is monitored by said electrical lap-guiding element.